# MAC15 Series TRIAC - 400V - 800V







#### **Additional Information**



Resources

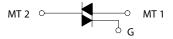




Accessories

Samples

### **Functional Diagram**



### **Description**

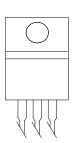
Designed primarily for full-wave ac control applications, such as solid-state relays, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied main terminal voltage with positive or negative gate triggering.

#### **Features**

- Blocking Voltage to 800 V
- All Diffused and Glass
   Passivated Junctions for
   Greater Parameter Uniformity
   and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Three Modes (MAC15 Series) or Four Modes (MAC15A Series)
- These Devices are Pb-Free and are RoHS Compliant

#### **Pin Out**







# **MAC15 Series** TRIAC - 400V - 800V

## **Maximum Ratings** (TJ = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Peak Repetitive Off-State Voltage (Note 1) (Gate Open, Sine Wave 50 to 60 Hz, T <sub>J</sub> = -40° to 125°C)	MAC15A6G MAC15-8G, MAC15A8G MAC15-10G, MAC15A10G	V <sub>DRM</sub> , V <sub>RRM</sub>	400 600 800	V
On-State RMS Current (Full Cycle Sine Wave, 50 to 60 H:	$z, T_{c} = 80^{\circ}C)$	I <sub>T (RMS)</sub>	15	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Non-Repetitive Surge Sine Non-Reptitive S	Nave, 60 Hz, $T_c = 80$ °C)	I <sub>TSM</sub>	150	А
Peak Gate Voltage (Pulse Width $\leq$ 1.0 µsec; $T_c = 90$ °C)		$V_{GM}$	10	V
Circuit Fusing Consideration (t = 8.3 ms)		l²t	93	A²sec
Peak Gate Power ( $T_c = 80^{\circ}\text{C}$ , Pulse Width = 1.0 µs)		$P_{GM}$	20	W
Peak Gate Current (Pulse Width $\leq 1.0 \mu sec; T_c = 90^{\circ}C$ )		I <sub>GM</sub>	2.0	А
Average Gate Power (t = 8.3 ms, $T_c = 80$ °C)		P <sub>G (AV)</sub>	0.5	W
Operating Junction Temperature Range	$T_{J}$	-40 to +125	°C	
Storage Temperature Range		T <sub>stg</sub>	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the

#### **Thermal Characteristics**

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R <sub>ejc</sub> R <sub>eja</sub>	2.0 62.5	°C/W
Maximum Lead Temperature for Soldering Purpose	s, 1/8" from case for 10 seconds	$T_L$	260	°C

### **Electrical Characteristics - OFF** (TJ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T <sub>1</sub> = 25°C	I <sub>DRM</sub> ,	-	-	0.01	mΛ
$(V_D = V_{DRM} = V_{RRM}; Gate Open)$	T <sub>J</sub> = 125°C	I <sub>RRM</sub>	-	-	2.0	mA

## **Electrical Characteristics - ON** (TJ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic			Min	Тур	Max	Unit
Peak On-State Voltage (Note 2) (I <sub>TM</sub> = ±21 A Peak)		$V_{TM}$	-	1.3	1.6	V
0 + T' 0 +	MT2(+), G(+)		-	-	50	
Gate Trigger Current (Continuous dc)	MT2(+), G(-)		-	-	50	mA
$(V_D = 12 \text{ V}, R_I = 100 \Omega)$	MT2(-), G(-)	GT	-	-	50	IIIA
$(v_D - 12 v, H_L - 100 \Omega)$	MT2(-), G(+)		-	-	75	
0 . T: 1/4	MT2(+), G(+)		-	0.9	2	
Gate Trigger Voltage (Continuous dc)	MT2(+), G(-)	\/	-	0.9	2	V
$(V_D = 12 \text{ V}, R_I = 100 \Omega)$	MT2(-), G(-)	V <sub>GT</sub>	-	1.1	2	V
$(V_D - 12 V, 11_L - 100 \Omega)$	MT2(-), G(+)		-	1.4	2.5	
O . N . T:	MT2(+), G(+)		0.2	-	-	
Gate Non-Trigger Voltage	MT2(+), G(-)	\/	0.2	-	-	V
$(T_J = 110^{\circ}C)$ $(V_D = 12 \text{ V}, R_I = 100 \Omega)$	MT2(-), G(-)	$V_{GD}$	0.2	-	-	V
$(V_D - 12 V, H_L - 100 \Omega)$	MT2(-), G(+)		0.2	-	-	
Holding Current ( $V_D = 12 V_{dc'}$ Gate Open, Initiating Current = ±200 mA))		l <sub>H</sub>	-	6.0	40	mA
Turn-On Time (VD = Rated VDRM, ITM = 17 A) (IGT = 120 mA, Rise Time = 0.1 μs, Pulse Width = 2 μs)		tgt	-	1.5	-	μs



Recommended Operating Conditions may affect device reliability.

1. V<sub>ISBM</sub> and V<sub>ISBM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

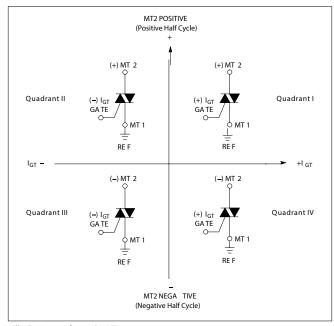
## **Dynamic Characteristics**

Characteristic	Symbol	Min	Тур	Max	Unit
Critical Rate of Rise of Commutation Voltage ( $V_D = Rated V_{DRM}$ , $I_{TM} = 21 A$ , Commutating di/dt = 7.6 A/ms, Gate Unenergized, $I_C = 80^{\circ}C$ )	dV/dt	_	5.0	_	V/µs

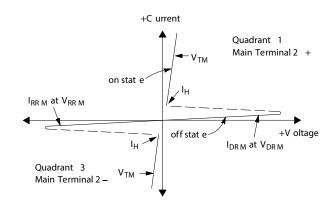
## **Voltage Current Characteristic of SCR**

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
$V_{_{\mathrm{RRM}}}$	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
$V_{TM}$	Maximum On State Voltage
I <sub>H</sub>	Holding Current

#### **Quadrant Definitions for a Triac**



All polarities are referenced to MT1.
With in-phase signals (using standard AC lines) quadrants I and III are used



**Figure 1. RMS Current Derating** 

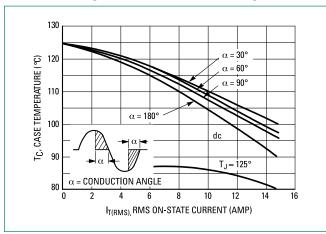


Figure 2. On-State Power Dissipation

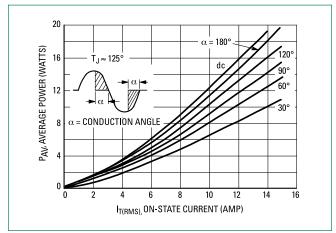
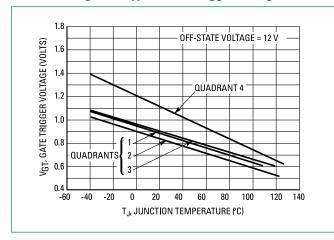


Figure 3. Typical Gate Trigger Voltage



**Figure 4. Typical Gate Trigger Current** 

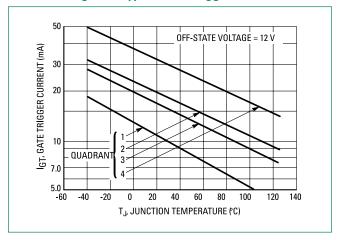
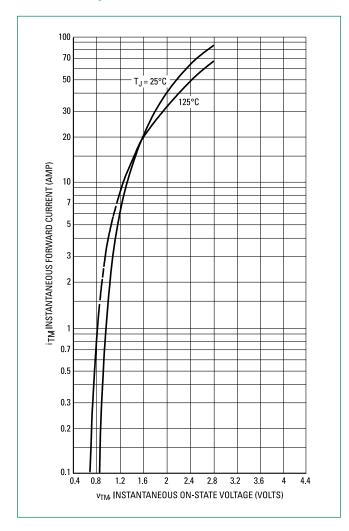




Figure 5. On-State Characteristics



**Figure 6. Typical Holding Current** 

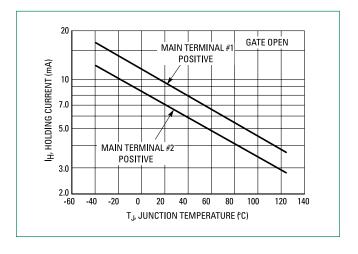
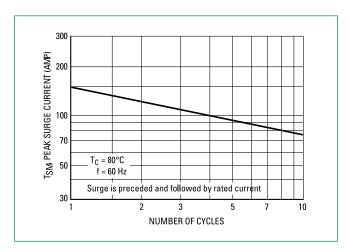
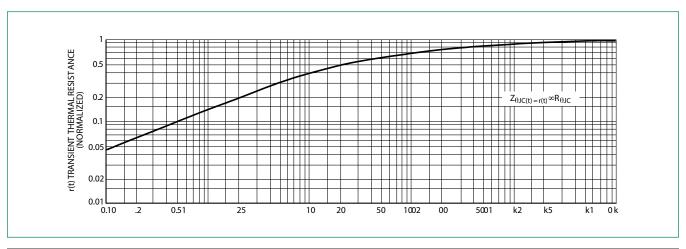


Figure 7. Maximum Non-Repetitive Surge Current



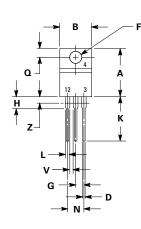
**Figure 8. Thermal Response** 

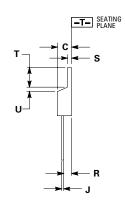




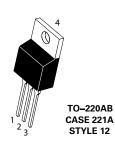
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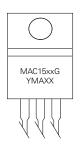
#### **Dimensions**





### **Part Marking System**





xx =See Table on Page 2 Y =Year M =Month A =Assembly Site

XX =Lot Serial Code G =Pb-Free Package

D:	Inches Dim		Millin	neters
DIM	Min	Max	Min	Max
Α	0.590	0.620	14.99	15.75
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
Н	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
K	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
N	0.195	0.205	4.95	5.21
Q	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	-	1.15	-
Z	-	0.080	-	2.04

Pin Assignment			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	Main Terminal 2		

### **Ordering Information**

Device	Device Device Marking Package		Shipping
MAC15-8G	MAC15-8		
MAC15-10G	MAC1510	TO 000 A D	
MAC15A6G	MAC15A6	TO-220AB (Pb-Free)	1000 Units/Box
MAC15A8G	MAC15A8	(1.5.1100)	
MAC15A10G	MAC15A10		



Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own

<sup>1.</sup> Dimensioning and tolerancing per ansi y14.5m, 1982.

Controlling dimension: inch.
 Dimension z defines a zone where all body and lead irregularities are allowed.

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**Authorized Distributor** 

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# Littelfuse:

MAC15A8G MAC15A6G MAC15-8G MAC15-10G MAC15A10G